## Zibo Seno Electronic Engineering Co., Ltd.



# RS10005M - RS1010M



## 10A GLASS PASSIVATED BRIDGE RECTIFIER

## **Features**

- Glass Passivated Die Construction
- High Case Dielectric Strength of 1500V<sub>RMS</sub>
- Low Reverse Leakage Current
- Surge Overload Rating to 170A Peak
- Ideal for Printed Circuit Board Applications
- Plastic Material UL Flammability Classification 94V-0
- Lead Free:For RoHS / Lead Free Version

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RS-10M							
Dim	Min	Max					
Α	24.80	25.20					
В	14.70	15.30					
С	4.00 Nominal						
D	17.20	17.80					
E	0.90	1.10					
G	7.30	7.70					
Н	3.10 Ø	3.40 ∅					
J	3.30	3.70					
K	1.50	1.90					
L	9.30	9.70					
М	2.50	2.90					
N	3.40	3.80					
Р	4.40	4.80					
R	0.60	0.80					
All Dimensions in mm							

### **Mechanical Data**

Case: Molded Plastic

 Terminals: Plated Leads, Solderable per MIL-STD-202, Method 208

• Polarity: Molded on Body

Mounting: Through Hole for #6 ScrewMounting Torque: 5.0 in-lbs Maximum

Weight: 6.6 grams (approx.)Marking: Type Number

## **Maximum Ratings and Electrical Characteristics** @ T<sub>A</sub> = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic		RS 10005M	RS 1001M	RS 1002M	RS 1004M	RS 1006M	RS 1008M	RS 1010M	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	50	100	200	400	600	800	1000	V
RMS Reverse Voltage		35	70	140	280	420	560	700	V
Average Forward Rectified Output Current @ T <sub>C</sub> = 110°C		10							Α
Non-Repetitive Peak Forward Surge Current, 8.3 ms single half-sine-wave superimposed on rated load (JEDEC method)		170						А	
Forward Voltage per element @ I <sub>F</sub> = 5	0A V <sub>FM</sub>	1.05							V
$ \begin{array}{lll} \mbox{Peak Reverse Current} & \mbox{@T}_{\mbox{C}} = 25^{\circ}\mbox{C} \\ \mbox{at Rated DC Blocking Voltage} & \mbox{@T}_{\mbox{C}} = 125^{\circ}\mbox{C} \\ \end{array} $		2.0 500						μА	
I <sup>2</sup> t Rating for Fusing (t < 8.3ms) (Note 1)		120							A <sup>2</sup> s
Typical Junction Capacitance per Element (Note 2)		55							pF
Typical Thermal Resistance, Junction to Case (Note 3)		1.4						°C/W	
Operating and Storage Temperature Range		-55 to +150						°C	

Notes:

- 1. Non-repetitive, for t > 1.0ms and < 8.3ms.
- 2. Measured at 1.0 MHz and applied reverse voltage of 4.0V DC.
- 3. Thermal resistance from junction to case per element. Unit mounted on 150 x 150 x 1.6mm copper plate heat sink.

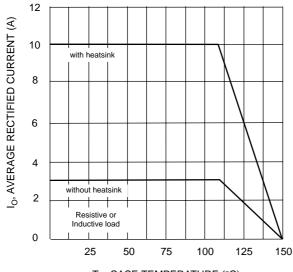
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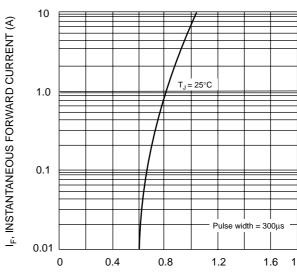
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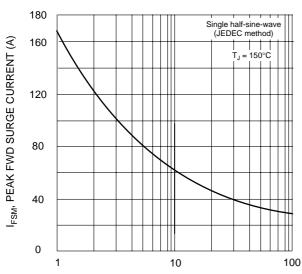




T<sub>C</sub>, CASE TEMPERATURE (°C) Fig. 1 Forward Current Derating Curve



V<sub>F</sub>, INSTANTANEOUS FORWARD VOLTAGE (V) Fig. 2 Typical Forward Characteristics (per element)



NUMBER OF CYCLES AT 60 Hz Fig. 3 Maximum Non-Repetitive Surge Current

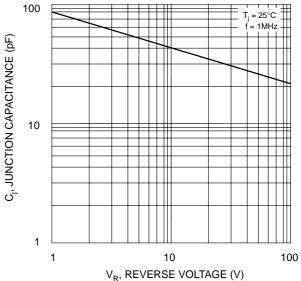
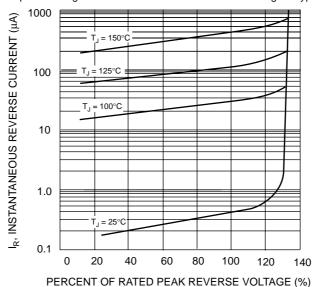


Fig. 4 Typical Junction Capacitance



PERCENT OF RATED PEAK REVERSE VOLTAGE (%) Fig. 5 Typical Reverse Characteristics